Vishay Semiconductors

Silicon PIN Photodiode



DESCRIPTION

TEMD7100X01 is a high speed and high sensitive PIN photodiode. It is a miniature surface mount device (SMD) including the chip with a 0.23 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength of 830 nm to 950 nm.

FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- Radiant sensitive area (in mm²): 0.23
- High radiant sensitivity
- Daylight blocking filter matched with 830 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 60^{\circ}$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- AEC-Q101 qualified
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- High speed photo detector
- Infrared remote control
- Infrared data transmission
- Photo interrupters
- Shaft encoders

PRODUCT SUMMARY			
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.5} (nm)
TEMD7100X01	3	± 60	750 to 1050

Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TEMD7100X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805	

Note

• MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	60	V
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	215	mW
Junction temperature		Тj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	Acc. reflow solder profile fig. 8	T _{sd}	260	°C
Thermal resistance junction/ambient	Acc. J-STD-051	R _{thJA}	270	K/W

Document Number: 81960 Rev. 1.2, 28-Sep-10





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BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1		V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	60			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		1	3	nA
Diode capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	CD		4		pF
	$V_{R} = 5 V, f = 1 MHz, E = 0$	CD		1.3		pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	l _k		3		μA
Temperature coefficient of I_k	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	TK _{lk}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \\ V_R = 5 \text{ V}$	I _{ra}	2.4	3	3.6	μA
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ _p		950		nm
Range of spectral bandwidth		λ _{0.5}		750 to 1050		nm
Rise time	$V_{R} = 10 \text{ V}, \text{R}_{L} = 1 \text{k}\Omega, \\ \lambda = 820 \text{ nm}$	t _r		100		ns
Fall time	$V_{\rm R} = 10 \text{ V}, \text{ R}_{\rm L} = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t _f		100		ns

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

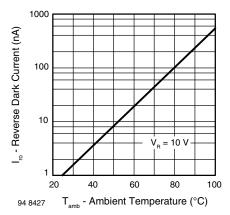


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

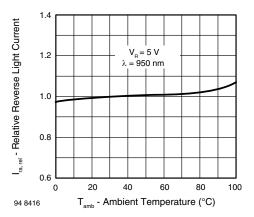


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



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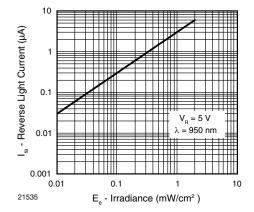


Fig. 3 - Reverse Light Current vs. Irradiance

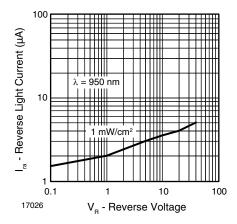


Fig. 4 - Reverse Light Current vs. Reverse Voltage

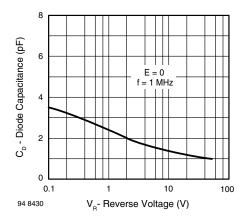


Fig. 5 - Diode Capacitance vs. Reverse Voltage

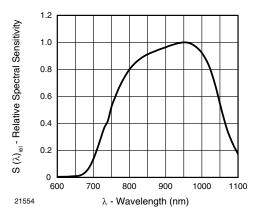


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

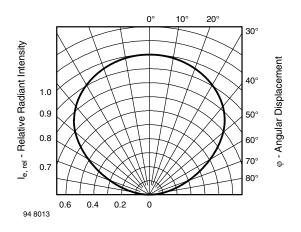


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

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REFLOW SOLDER PROFILE

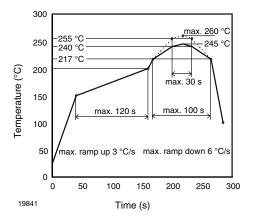


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

PACKAGE DIMENSIONS in millimeters

DRYPACK

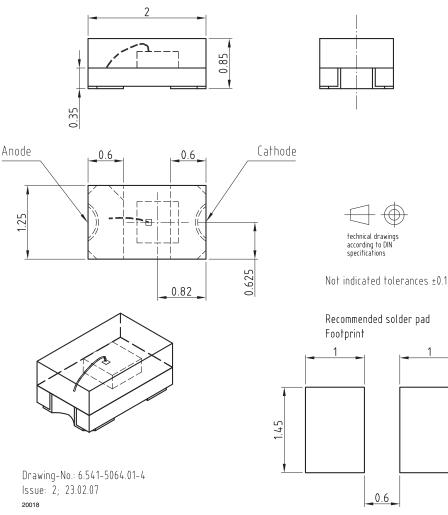
Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label: Floor life: 168 h Conditions: $T_{amb} < 30$ °C, RH < 60 % Moisture sensitivity level 3, acc. to J-STD-020.

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.



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For technical questions, contact: <u>detectortechsupport@vishay.com</u>

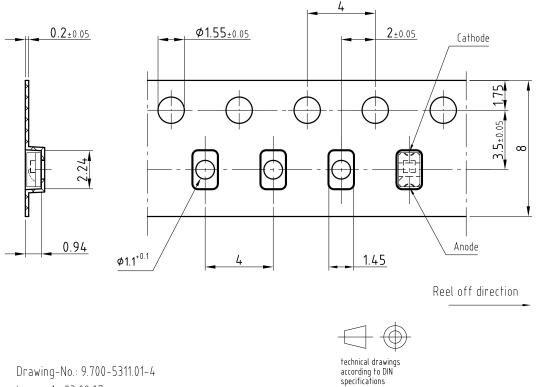
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BLISTER TAPE DIMENSIONS in millimeters



Drawing-No.: 9.700-5311.01-4 Issue: 1; 23.02.07 21501

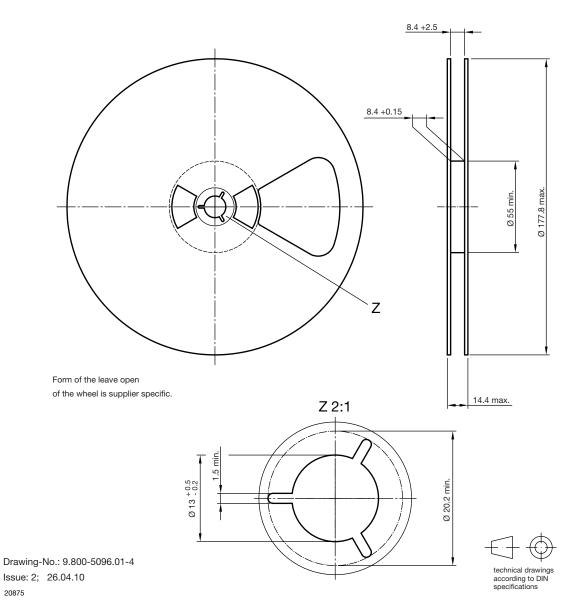
Not indicated tolerances ±0.1

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REEL DIMENSIONS in millimeters





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